TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

2SJ201

High Power Amplifier Application

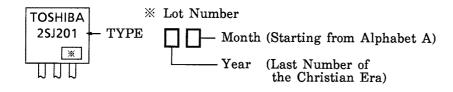
Unit: mm

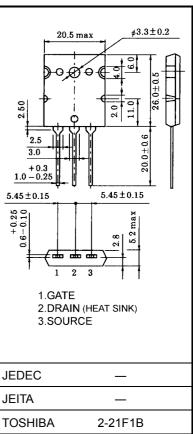
• Complementary to 2SK1530

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	-200	V
Gate-source voltage	V_{GSS}	±20	V
Drain current (Note 1)	I _D	-12	Α
Drain power dissipation (Tc = 25°C)	P_{D}	150	W
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	-55~150	°C

Marking





Weight: 9.75 g (typ.)

Electrical Characteristics (Ta = 25°C)

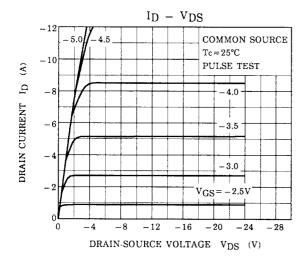
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} = -200 V, V _{GS} = 0	_	_	-1.0	mA
Gate leakage current	I _{GSS}	V _{DS} = 0, V _{GS} = ±20 V	_	_	±0.5	μΑ
Drain-source breakdown voltage	V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0$	-200	_	_	V
Gate-source cut-off voltage (Note 2)	V _{GS (OFF)}	V _{DS} = -10 V, I _D = -0.1 A	-0.8	_	-2.8	V
Drain-source saturation voltage	V _{DS} (ON)	I _D = -8 A, V _{GS} = -10 V	_	-2.0	-5.0	V
Forward transfer admittance	Y _{fs}	V _{DS} = -10 V, I _D = -5 A	_	5.0	_	S
Input capacitance	C _{iss}	$V_{DS} = -30 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	1500	_	
Output capacitance	Coss	$V_{DS} = -30 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	430	_	pF
Reverse transfer capacitance	C _{rss}	$V_{DS} = -30 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	230	_	

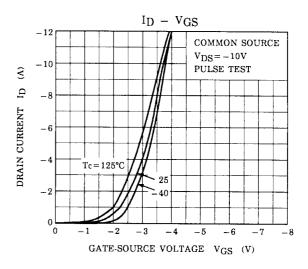
Note 1: Please use devices on condition that the channel temperature is below 150°C.

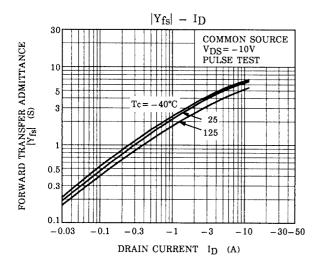
Note 2: V_{GS (OFF)} Classification O: -0.8~-1.6, Y: -1.4~-2.8

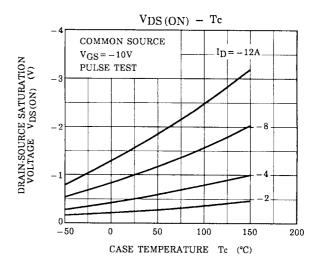
This transistor is an electrostatic sensitive device.

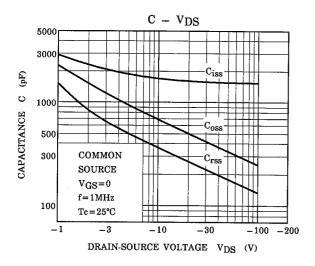
Please handle with caution.

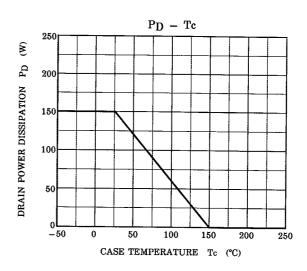




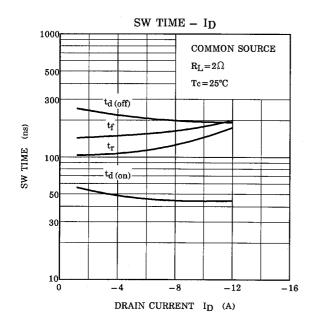


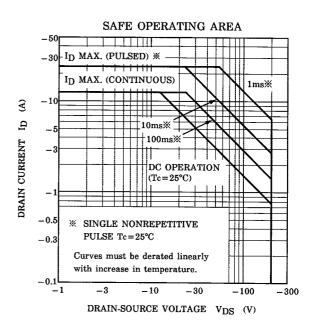




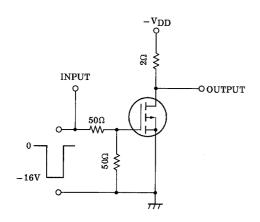


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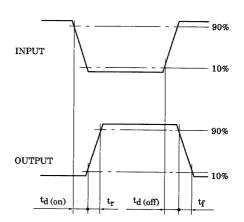




Switching Time Test Circuit



Waveforms



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